

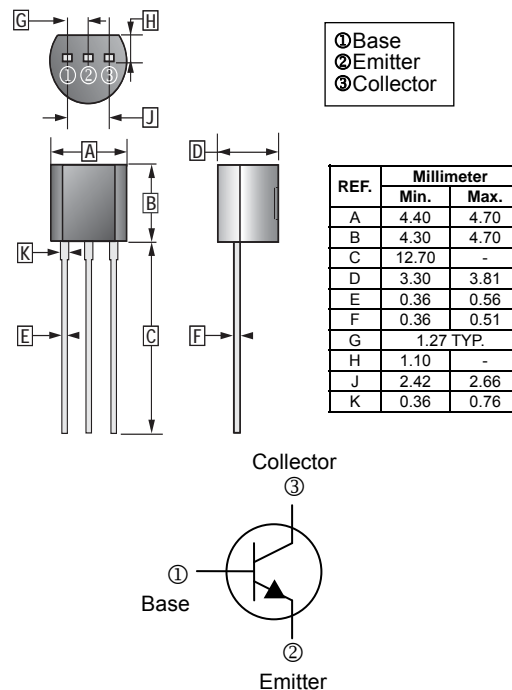
RoHS Compliant Product

A suffix of "-C" specifies halogen & lead-free

## FEATURES

- Amplifier dissipation NPN Silicon

TO-92



## ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	$V_{CBO}$	50	V
Collector to Emitter Voltage	$V_{CEO}$	45	V
Emitter to Base Voltage	$V_{EBO}$	4	V
Collector Current - Continuous	$I_C$	50	mA
Collector Power Dissipation	$P_C$	300	mW
Junction, Storage Temperature	$T_J, T_{STG}$	125, -55~125	$^\circ\text{C}$

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	50	-	-	V	$I_C=100\mu\text{A}, I_E=0$
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	45	-	-	V	$I_C=10\text{mA}, I_B=0$
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	4	-	-	V	$I_E=100\mu\text{A}, I_C=0$
Collector Cut - Off Current	$I_{CBO}$	-	-	0.1	$\mu\text{A}$	$V_{CB}=50\text{V}, I_E=0$
Emitter Cut - Off Current	$I_{EBO}$	-	-	0.1	$\mu\text{A}$	$V_{EB}=3\text{V}, I_C=0$
DC Current Gain	$h_{FE}$	40	-	140		$V_{CE}=12.5\text{V}, I_C=12.5\text{mA}$
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	-	-	0.2	V	$I_C=15\text{mA}, I_B=1.5\text{mA}$
Base to Emitter voltage	$V_{BE(sat)}$	-	-	1.5	V	$I_C=15\text{mA}, I_B=1.5\text{mA}$
Transition Frequency	$f_T$	300	-	-	MHz	$V_{CE}=12.5\text{V}, I_C=12.5\text{mA}$
Collector Output Capacitance	$C_{ob}$	-	-	2	pF	$V_{CB}=10\text{V}, I_E=0, f=30\text{MHz}$

**CHARACTERISTIC CURVES**

